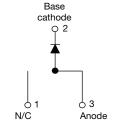
VS-8TQ080SPbF, VS-8TQ100SPbF

Vishay Semiconductors

High Performance Schottky Rectifier, 8 A



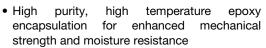


TO-263AB	(D ² PAK)

PRODUCT SUMMARY							
Package	TO-263AB (D ² PAK)						
I _{F(AV)}	8 A						
V_{R}	80 V, 100 V						
V _F at I _F	0.72 V						
I _{RM} max.	7 mA at 125 °C						
T_J max.	175 °C						
Diode variation	Single die						
Eas	7.5 m.l						

FEATURES

- 175 °C T_J operation
- Low forward voltage drop
- · High frequency operation





COMPLIANT HALOGEN FREE

- Guard ring for enhanced ruggedness and long term reliability
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION

The VS-8TQ... Schottky rectifier series has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 175 °C junction temperature. Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

MAJOR RATINGS AND CHARACTERISTICS									
SYMBOL CHARACTERISTICS VALUES UN									
I _{F(AV)}	Rectangular waveform	8	Α						
V _{RRM}	Range	80, 100	V						
I _{FSM}	t _p = 5 μs sine	850	Α						
V _F	8 A _{pk} , T _J = 125 °C	0.58	V						
TJ	Range	-55 to +175	°C						

VOLTAGE RATINGS									
PARAMETER	SYMBOL	VS-8TQ080SPbF	VS-8TQ100SPbF	UNITS					
Maximum DC reverse voltage	V_{R}	80	100	V					
Maximum working peak reverse voltage	V_{RWM}	00	100	V					

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST COND	VALUES	UNITS					
Maximum average forward current See fig. 5	I _{F(AV)}	50 % duty cycle at T _C = 157 °C, rectangular waveform		8	Α				
Maximum peak one cycle non-repetitive surge current	l	5 µs sine or 3 µs rect. pulse	Following any rated load condition and with rated	850	А				
See fig. 7	I _{FSM}	10 ms sine or 6 ms rect. pulse	V _{RRM} applied	230					
Non-repetitive avalanche energy	E _{AS}	T _J = 25 °C, I _{AS} = 0.50 A, L = 60 mH		7.50	mJ				
Repetitive avalanche current	I _{AR}	Current decaying linearly to zero in 1 μ s Frequency limited by T _J maximum V _A = 1.5 x V _R typical		0.50	Α				



VS-8TQ080SPbF, VS-8TQ100SPbF

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ELECTRICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CO	VALUES	UNITS				
Maximum forward voltage drop See fig. 1		8 A	T _{.1} = 25 °C	0.72				
	V _{FM} ⁽¹⁾	16 A	1j=25 C	0.88	V			
		8 A	T 105 00	0.58				
		16 A	T _J = 125 °C	0.69	l			
Maximum reverse leakage current	1 (1)	T _J = 25 °C	V _B = Rated V _B	0.55	- mA			
See fig. 2	I _{RM} (1)	T _J = 125 °C	v _R = nateu v _R	7				
Maximum junction capacitance	C _T	V _R = 5 V _{DC} (test signal range 100 kHz to 1 MHz), 25 °C		500	pF			
Typical series inductance	L _S	Measured lead to lead 5 mm from package body		8	nH			
Maximum voltage rate of change	dV/dt	Rated V _R	10 000	V/µs				

Note

 $^{^{(1)}\,}$ Pulse width < 300 $\mu s,$ duty cycle < 2 %

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER		SYMBOL	SYMBOL TEST CONDITIONS		UNITS			
Maximum junction and storage temperature range		T _J , T _{Stg}		-55 to +175	°C			
Maximum thermal resistance, junction to case		R _{thJC}	DC operation See fig. 4	2.0	°C/W			
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth and greased		C/VV			
Approximate weight				2	g			
Approximate weight				0.07	OZ.			
Mayorting toway	minimum			6 (5)	kgf ⋅ cm			
Mounting torque	maximum			12 (10)	(lbf · in)			
Marking device			Case style D ² PAK	8TQ	080S			
			Case style D-PAN	8TQ	100S			

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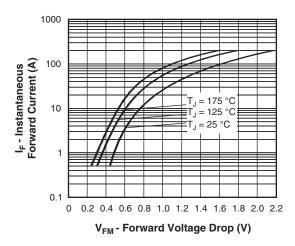


Fig. 1 - Maximum Forward Voltage Drop Characteristics

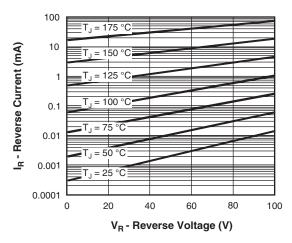


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

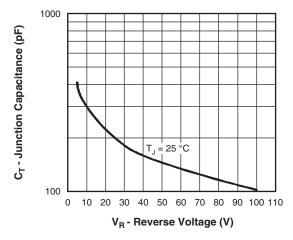


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

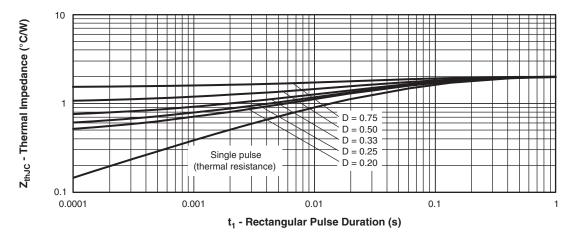


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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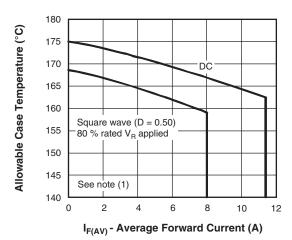


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

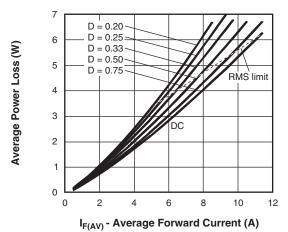


Fig. 6 - Forward Power Loss Characteristics

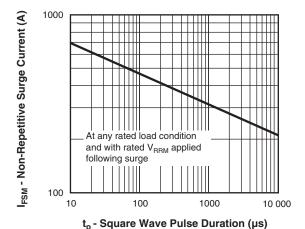


Fig. 7 - Maximum Non-Repetitive Surge Current

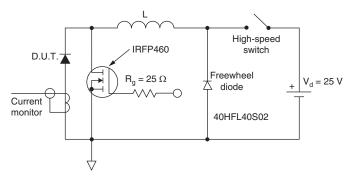


Fig. 8 - Unclamped Inductive Test Circuit

Note

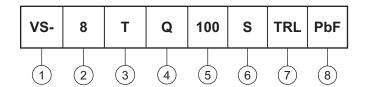
 $^{(1)}$ Formula used: T_C = T_J - (Pd + Pd_{REV}) x R_{thJC}; Pd = Forward power loss = I_{F(AV)} x V_{FM} at (I_{F(AV)}/D) (see fig. 6); Pd_{REV} = Inverse power loss = V_{R1} x I_R (1 - D); I_R at V_{R1} = 80 % rated V_R

VS-8TQ080SPbF, VS-8TQ100SPbF

Vishay Semiconductors

ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

Current rating (8 A)

Circuit configuration: T = TO-220

- Schottky "Q" series

5 - Voltage ratings - 080 = 80 V 100 = 100 V

6 - S = D²PAK

7 - • None = tube (50 pieces)

• TRL = tape and reel (left oriented)

• TRR = tape and reel (right oriented)

8 - PbF = lead (Pb)-free

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?95046					
Part marking information	www.vishay.com/doc?95054					
Packaging information	www.vishay.com/doc?95032					
SPICE models	www.vishay.com/doc?95291					



Vishay Semiconductors

D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES	NOTES	SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOIES	NOTES	STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100) BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC® outline TO-263AB



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Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

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